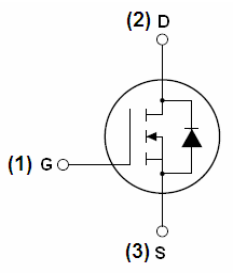
N-Channel Enhancement Mode Power MOSFET

Description

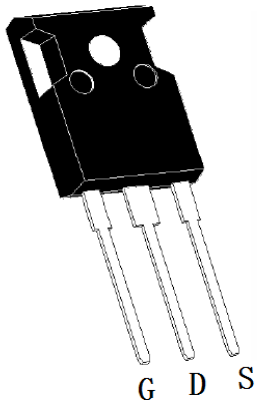
The FNK01N30T uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of other applications.



Schematic diagram

General Features

- V_{DSS} =100V,I_D =300A
  $R_{DS(ON)}$ < 3.3mΩ @ V_{GS}=10V （Typ：2.7mΩ）
- Good stability and uniformity with high E_{AS}
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation



TO-247 top view

Application

- DC motor drive
- High efficiency synchronous rectification in SMPS
- Uninterruptible power supply
- High speed power switching
- Hard switched and high frequency circuits

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
FNK01N30T	FNK01N30T	TO-247	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DSS}	100	V
Gate-Source Voltage	V_{GS}	±25	V
Drain Current-Continuous	I_D	300	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	200	A
Pulsed Drain Current	I_{DM}	1120	A
Maximum Power Dissipation	P_D	455	W
Derating factor		3.07	W/℃

Single pulse avalanche energy (Note 3)	E_{AS}	1600	mJ
Peak Diode Recovery dv/dt (Note 4)	dv/dt	10	V/ns
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case (Note 1)	$R_{\theta JC}$	0.33	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

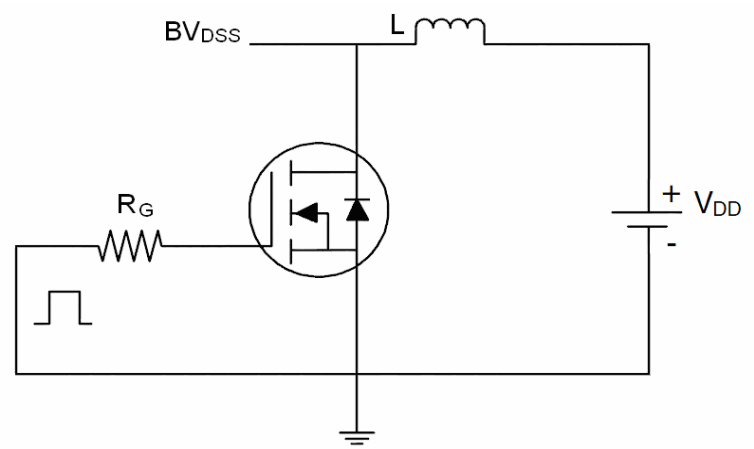
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	100	110	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±200	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	3.3	3.6	4.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=40A	-	2.7	3.3	mΩ
Forward Transconductance	g_{FS}	V_{DS}=25V,I_D=40A	310	-	-	S
Dynamic Characteristics						
Input Capacitance	C_{lss}	V_{DS}=25V,V_{GS}=0V, F=1.0MHz	-	17630	-	PF
Output Capacitance	C_{oss}		-	1645	-	PF
Reverse Transfer Capacitance	C_{rss}		-	1261	-	PF
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=50V,I_D=40A V_{GS}=10V,R_{GEN}=1.2Ω (Note2)	-	44.6	-	nS
Turn-on Rise Time	t_r		-	29.4	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	139.8	-	nS
Turn-Off Fall Time	t_f		-	36.4	-	nS
Total Gate Charge	Q_g	V_{DS}=30V,I_D=30A V_{GS}=10V	-	586	-	nC
Gate-Source Charge	Q_{gs}		-	123	-	nC
Gate-Drain Charge	Q_{gd}		-	184	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	V_{GS}=0V,I_S=40A	-	-	1.2	V
Reverse Recovery Time	t_{rr}	TJ = 25°C, IF = 40A di/dt = 100A/μs (Note2)	-	88.9	-	nS
Reverse Recovery Charge	Qrr		-	139	-	nC

Notes:

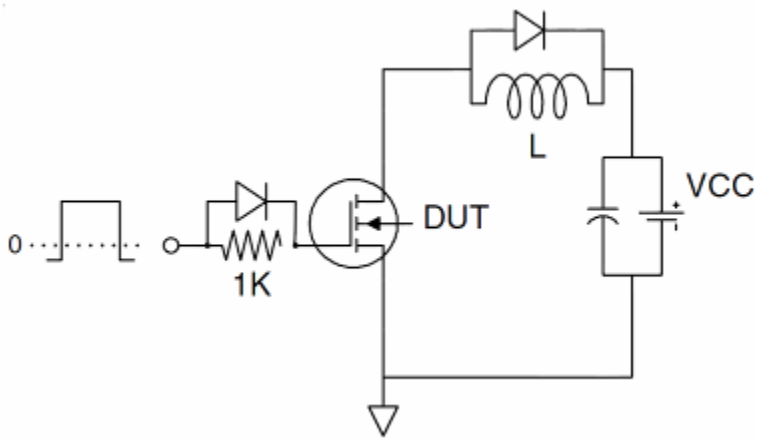
1. Surface Mounted on FR4 Board, t ≤ 10 sec.
2. Pulse Test: Pulse Width ≤ 400μs, Duty Cycle ≤ 2%.
3. EAS condition：Tj=25℃,V_{DD}=50V,V_G=10V,L=0.5mH,Rg=25Ω
4. I_{SD}≤125A, di/dt≤260A/μs, V_{DD}≤$V_{(BR)DSS}$，T_J ≤175°C

Test circuit

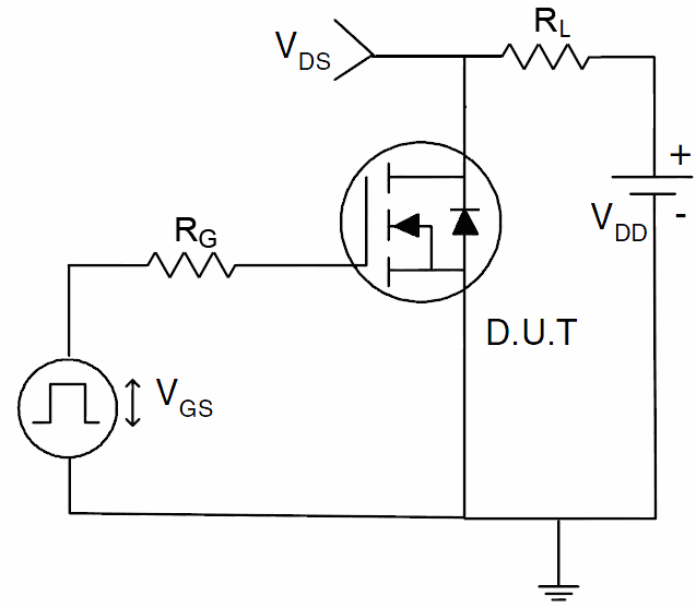
1）E_{AS} test Circuits



2）Gate charge test Circuit:



3）Switch Time Test Circuit：



Typical Electrical and Thermal Characteristics

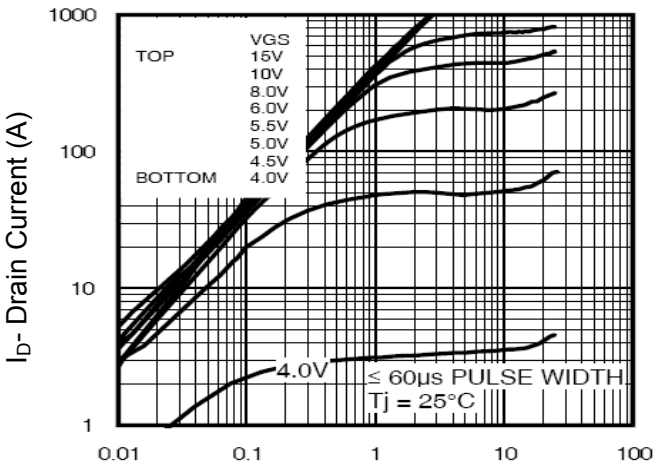


Figure 1 Output Characteristics

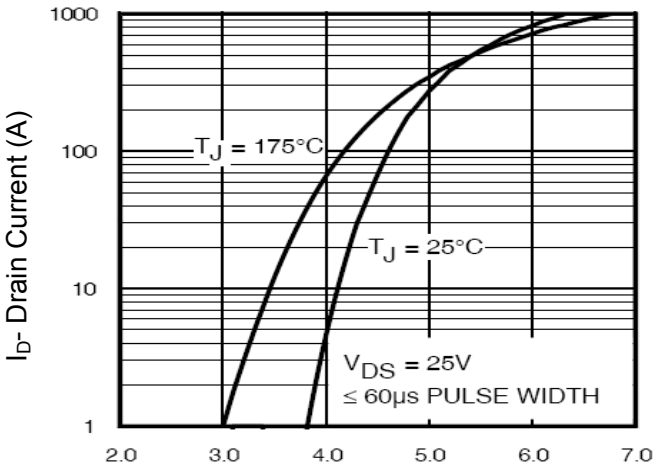


Figure 2 Transfer Characteristics

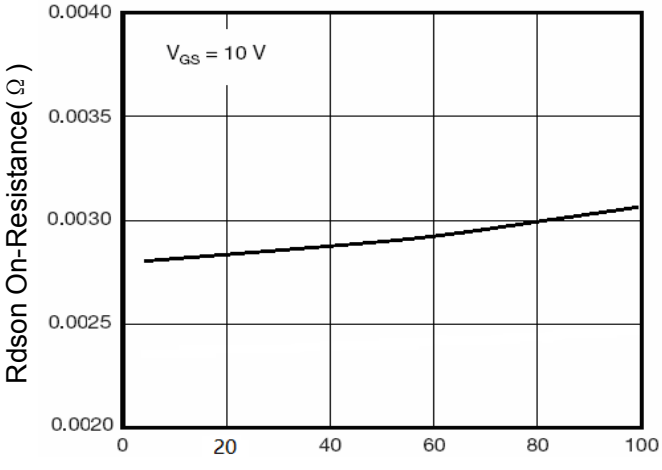


Figure 3 Rdson- Drain Current

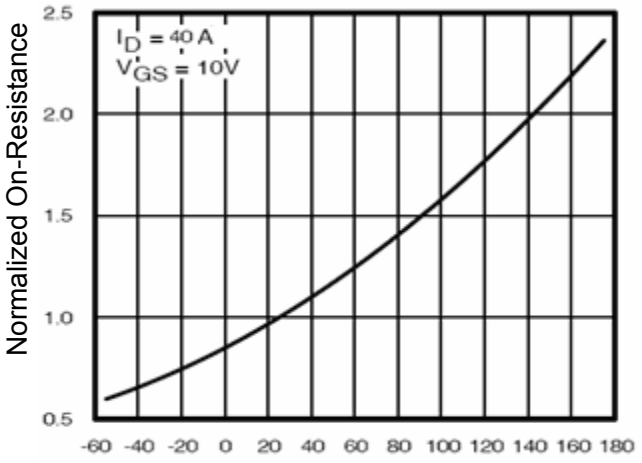


Figure 4 Rdson-JunctionTemperature

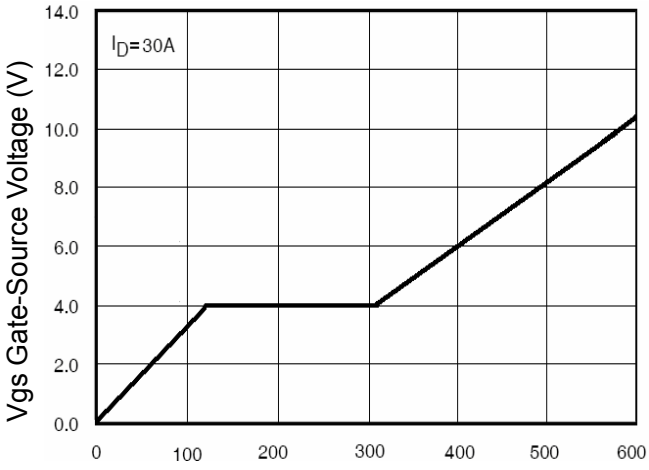


Figure 5 Gate Charge

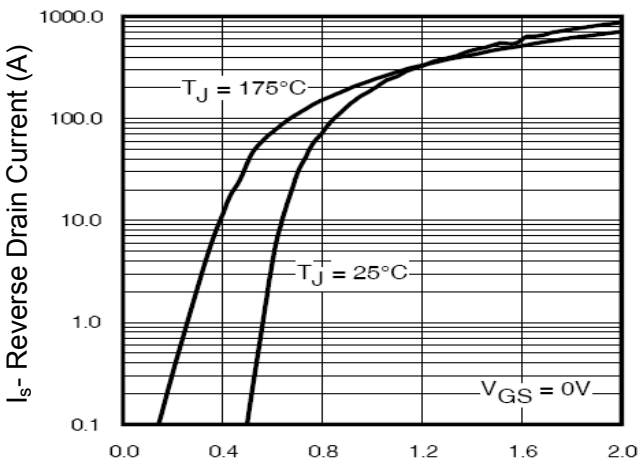


Figure 6 Source- Drain Diode Forward

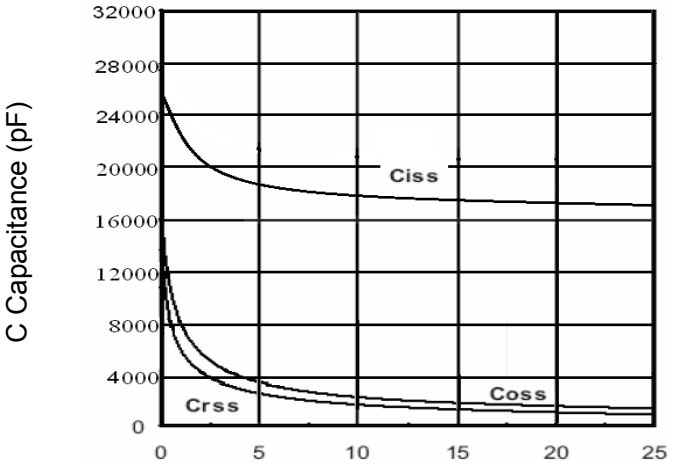


Figure 7 Capacitance vs Vds

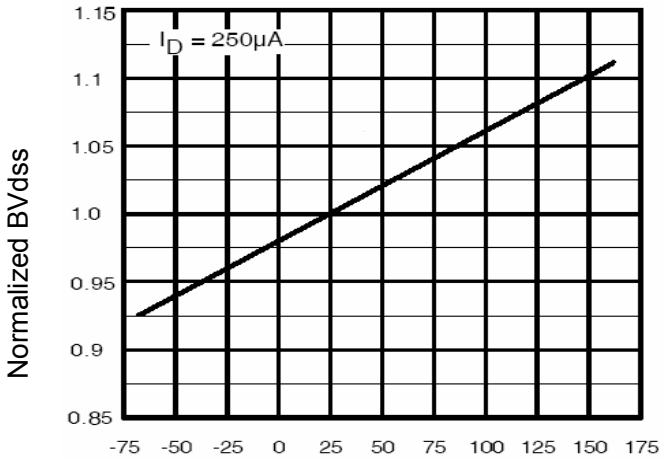


Figure 9 BV_{DSS} vs Junction Temperature

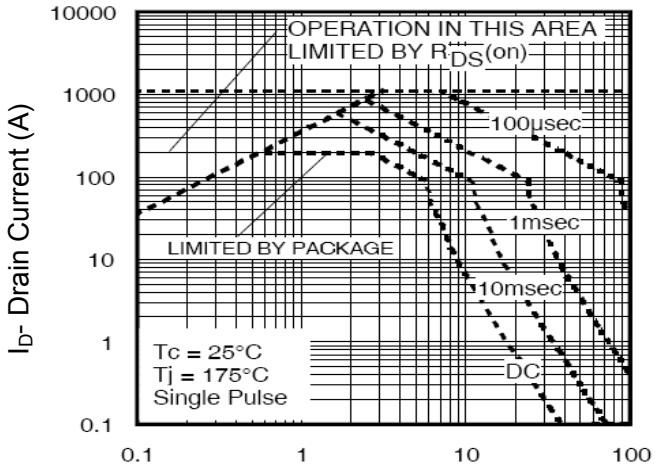


Figure 8 Safe Operation Area

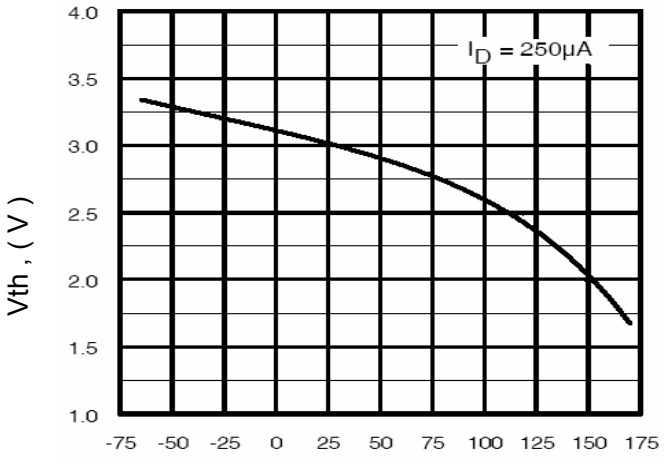


Figure 10 $V_{GS(th)}$ vs Junction Temperature

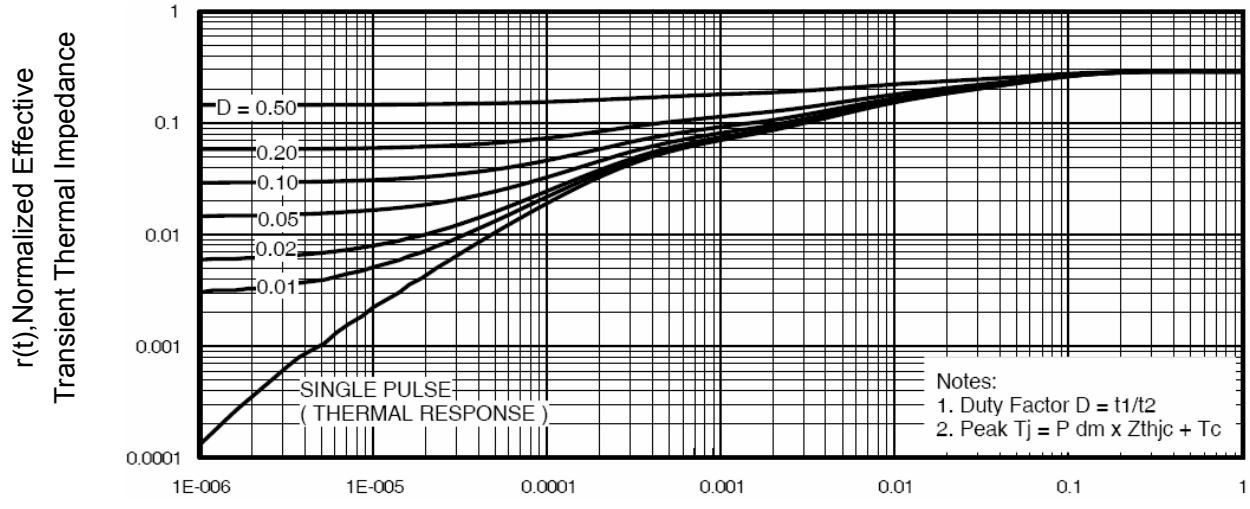
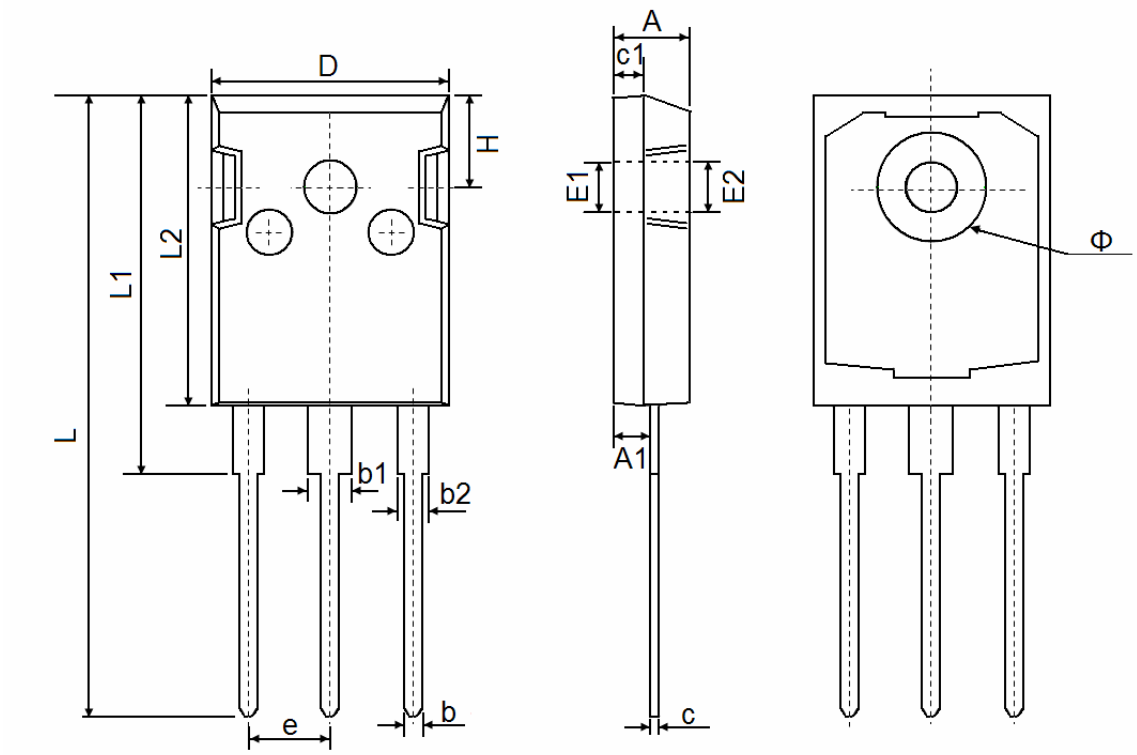


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-247 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.850	5.150	0.191	0.200
A1	2.200	2.600	0.087	0.102
b	1.000	1.400	0.039	0.055
b1	2.800	3.200	0.110	0.126
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.900	2.100	0.075	0.083
D	15.450	15.750	0.608	0.620
E1	3.500 REF		0.138 REF	
E2	3.600 REF		0.142 REF	
L	40.900	41.300	1.610	1.626
L1	24.800	25.100	0.976	0.988
L2	20.300	20.600	0.799	0.811
Φ	7.100	7.300	0.280	0.287
e	5.450 TYP		0.215 TYP	
H	5.980 REF		0.235 REF	

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